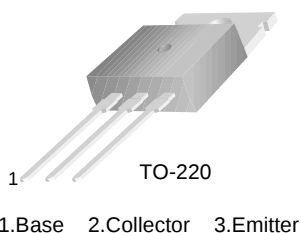


FJP3305

High Voltage Fast-Switching NPN Power Transistor

- High Voltage Capability
- High Switching Speed
- Suitable for Electronic Ballast and Switching Regulator



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current (DC)	4	A
I _{CP}	Collector Current (Pulse)	8	A
I _B	Base Current	2	A
P _C	Collector Dissipation (T _C = 25°C)	75	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 ~ 150	°C

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 500\mu\text{A}$, $I_E = 0$	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5\text{mA}$, $I_B = 0$	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 500\mu\text{A}$, $I_C = 0$	9			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 700\text{V}$, $I_E = 0$			1	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 9\text{V}$, $I_C = 0$			1	μA
h_{FE1} h_{FE2}	DC Current Gain *	$V_{CE} = 5\text{V}$, $I_C = 1\text{A}$ $V_{CE} = 5\text{V}$, $I_C = 2\text{A}$	19 8		35 40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 1\text{A}$, $I_B = 0.2\text{A}$ $I_C = 2\text{A}$, $I_B = 0.5\text{A}$ $I_C = 4\text{A}$, $I_B = 1\text{A}$			0.5 0.6 1.0	V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 1\text{A}$, $I_B = 0.2\text{A}$ $I_C = 2\text{A}$, $I_B = 0.5\text{A}$			1.2 1.6	V V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}$, $I_C = 0.5\text{A}$	4			MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$		65		pF
t_{ON}	Turn On Time	$V_{CC} = 125\text{V}$, $I_C = 2\text{A}$ $I_{B1} = -I_{B2} = 0.4\text{A}$ $R_L = 62.5\Omega$			0.8	μs
t_{STG}	Storage Time				4.0	μs
t_F	Fall Time				0.9	μs

* Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

h_{FE} Classification

Classification	H1	H2
h_{FE1}	19 ~ 28	26 ~ 35

Typical Performance Characteristics

Figure 1. Static Characteristic

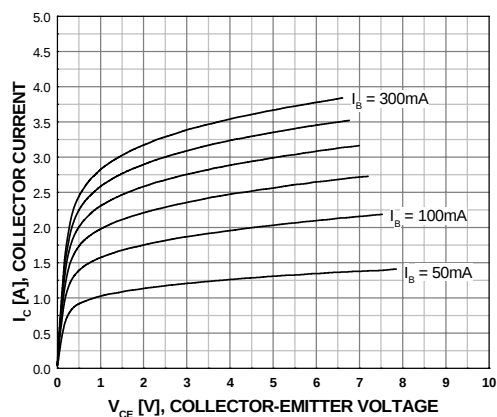


Figure 2. DC Current Gain (R-Grade)

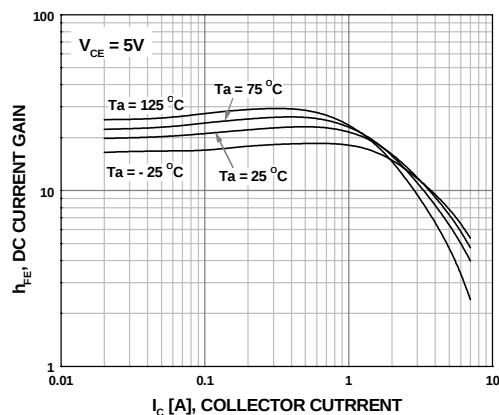


Figure 3. DC Current Gain (O-Grade)

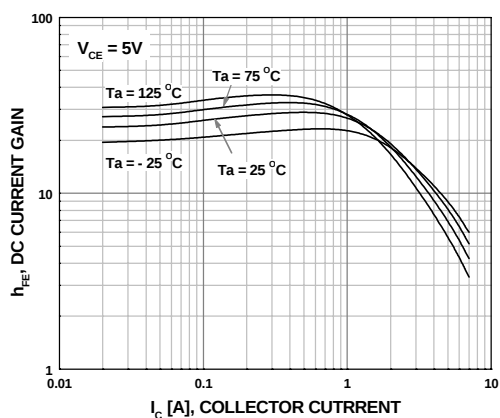


Figure 4. Saturation Voltage (R-Grade)

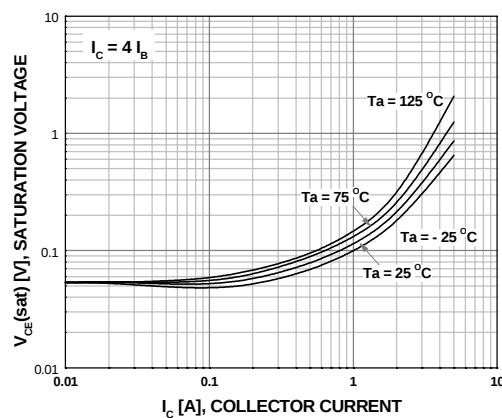


Figure 5. Saturatin Voltage (O-Grade)

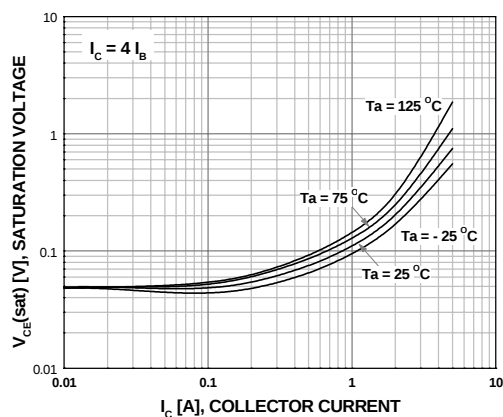
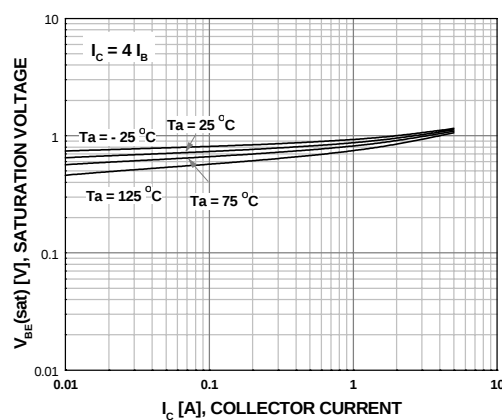


Figure 6. Saturation Voltage (R-Grade)



Typical Performance Characteristics (Continued)

Figure 7. Saturation Voltage (O-Grade)

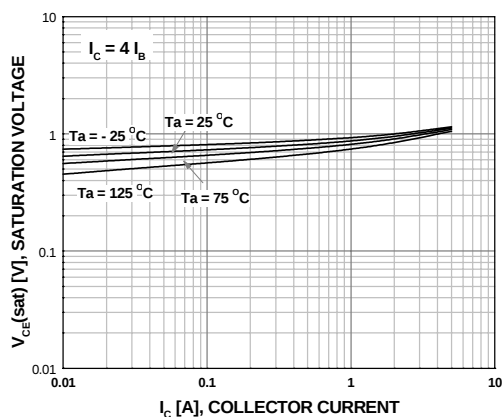


Figure 8. Switching Time

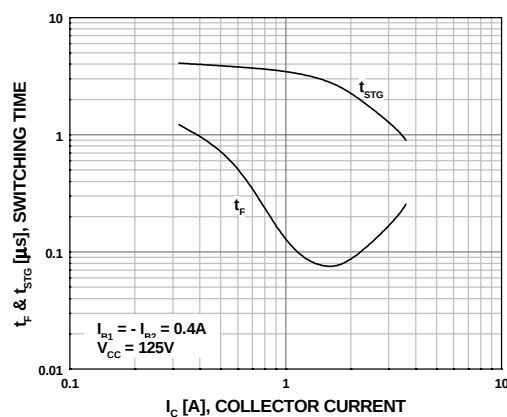


Figure 9. Reverse Biased Safe Operating Area

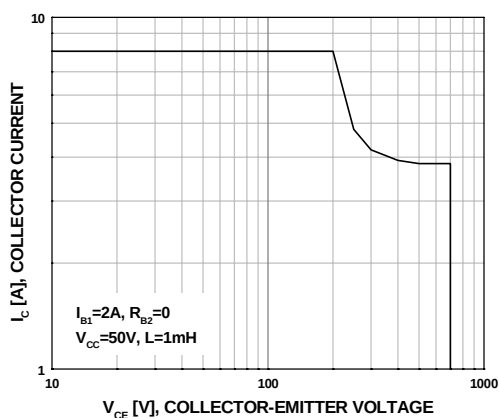


Figure 10. Forward Biased Safe Operating Area

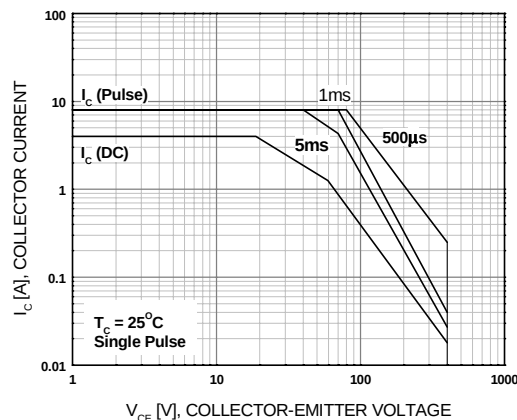
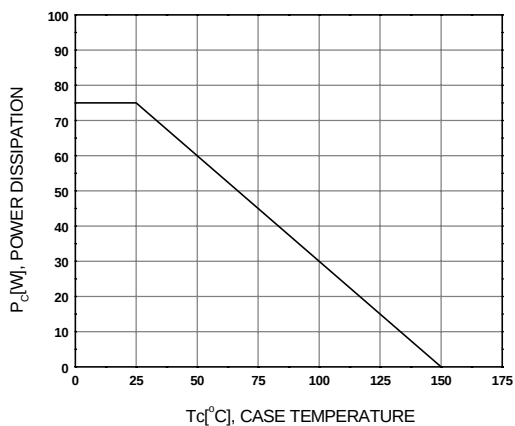
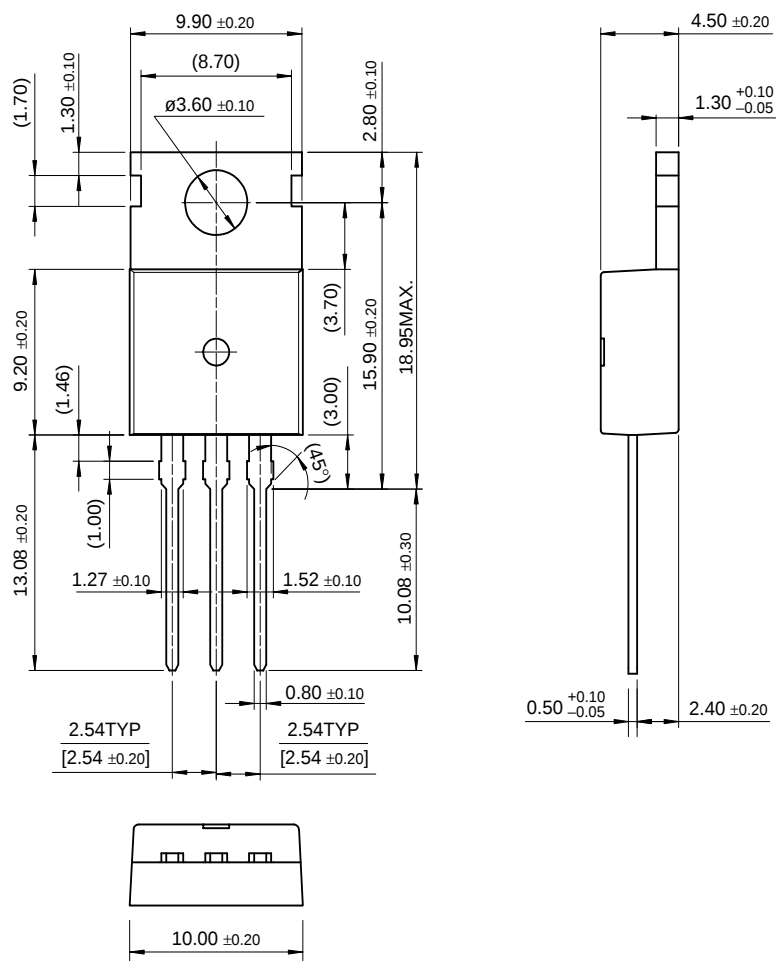


Figure 11. Power Derating



Mechanical Dimensions

TO-220



Dimensions in Millimeters

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